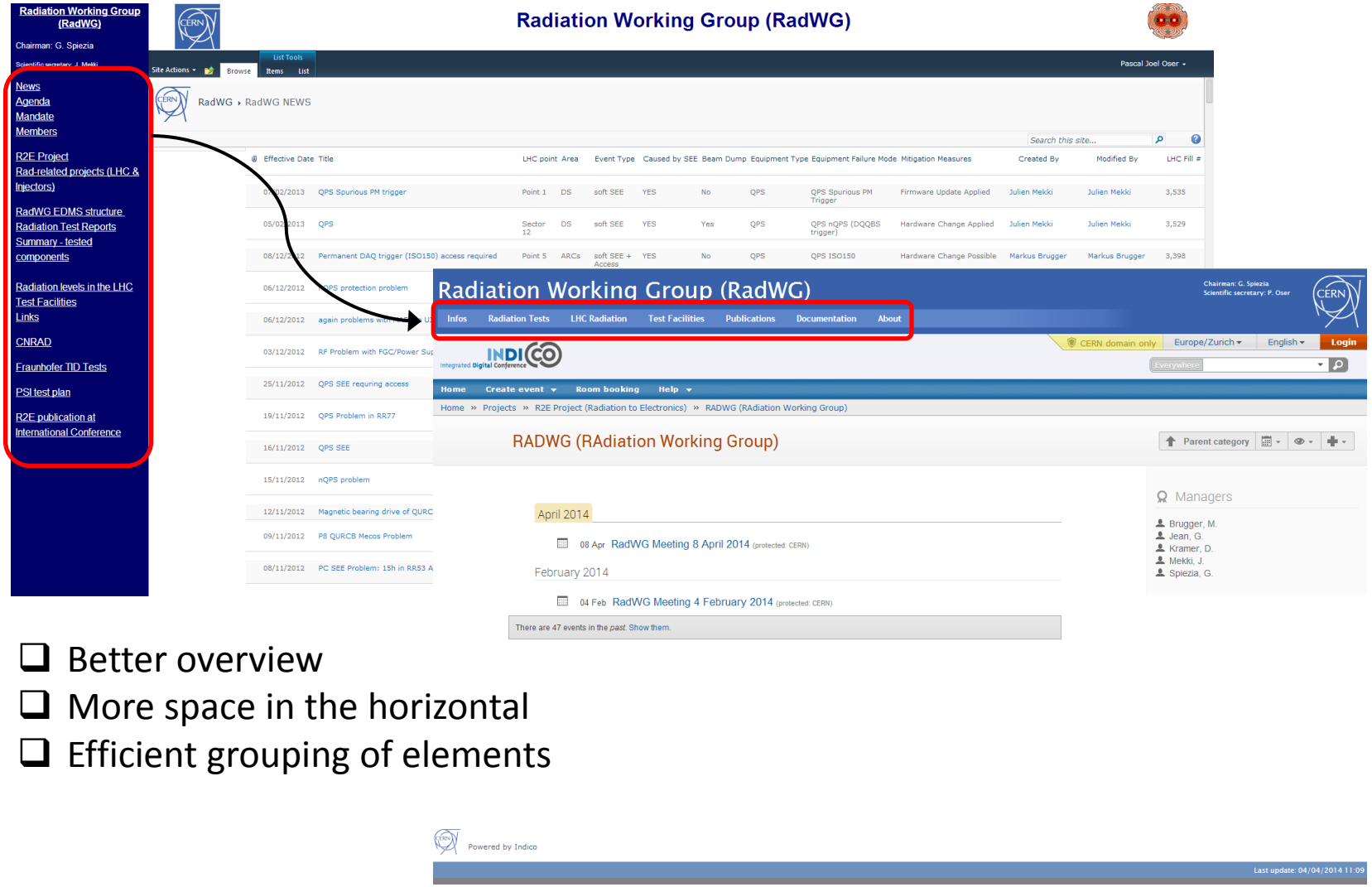
Introduction to the new RadWG website

P. Oser, EN-STI-ECE

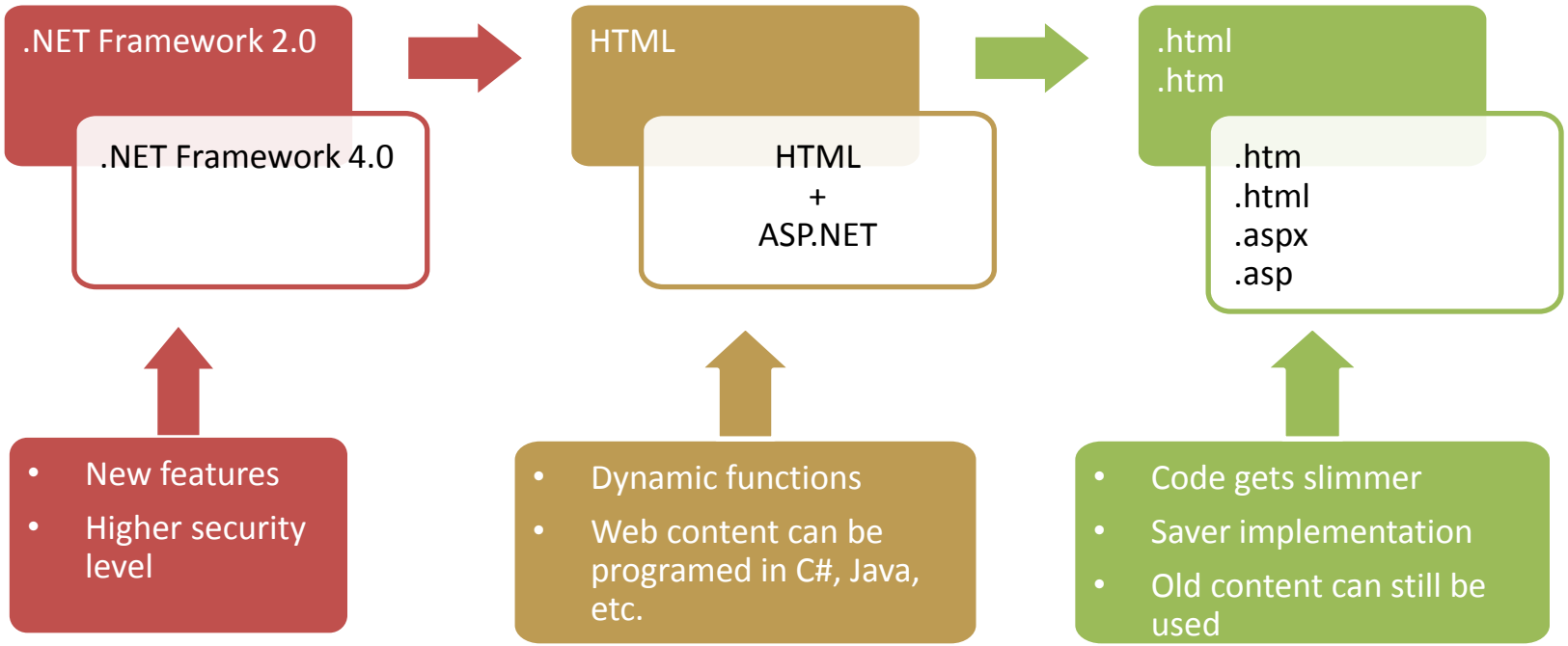
Why a new design?



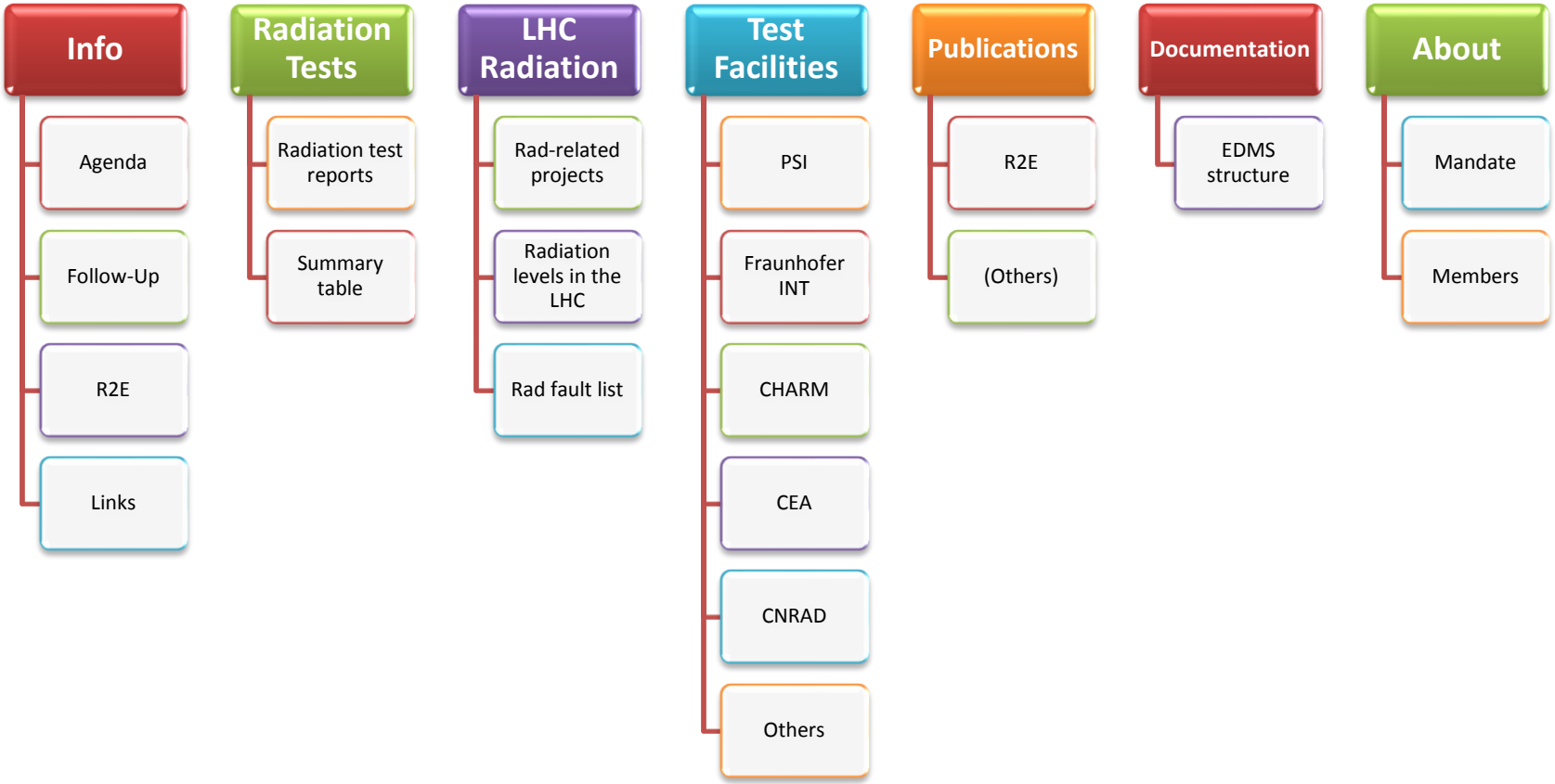
- Better overview
- More space in the horizontal
- Efficient grouping of elements

What comes with the new design?

- New and more modern look ☺
- Ported the ‘old’ framework to a more actual one



What is new?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Agenda
Follow-Up
R2E
Links
Radiation Tests
Radiation test reports
Summary table
LHC Radiation
Rad-related projects
Radiation levels in the LHC
Rad fault list
Test Facilities
PSI
Fraunhofer INT
CHARM
CEA
CNRAD
Others
Publications
R2E
(Others)
Documentation
EDMS structure
About
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Members

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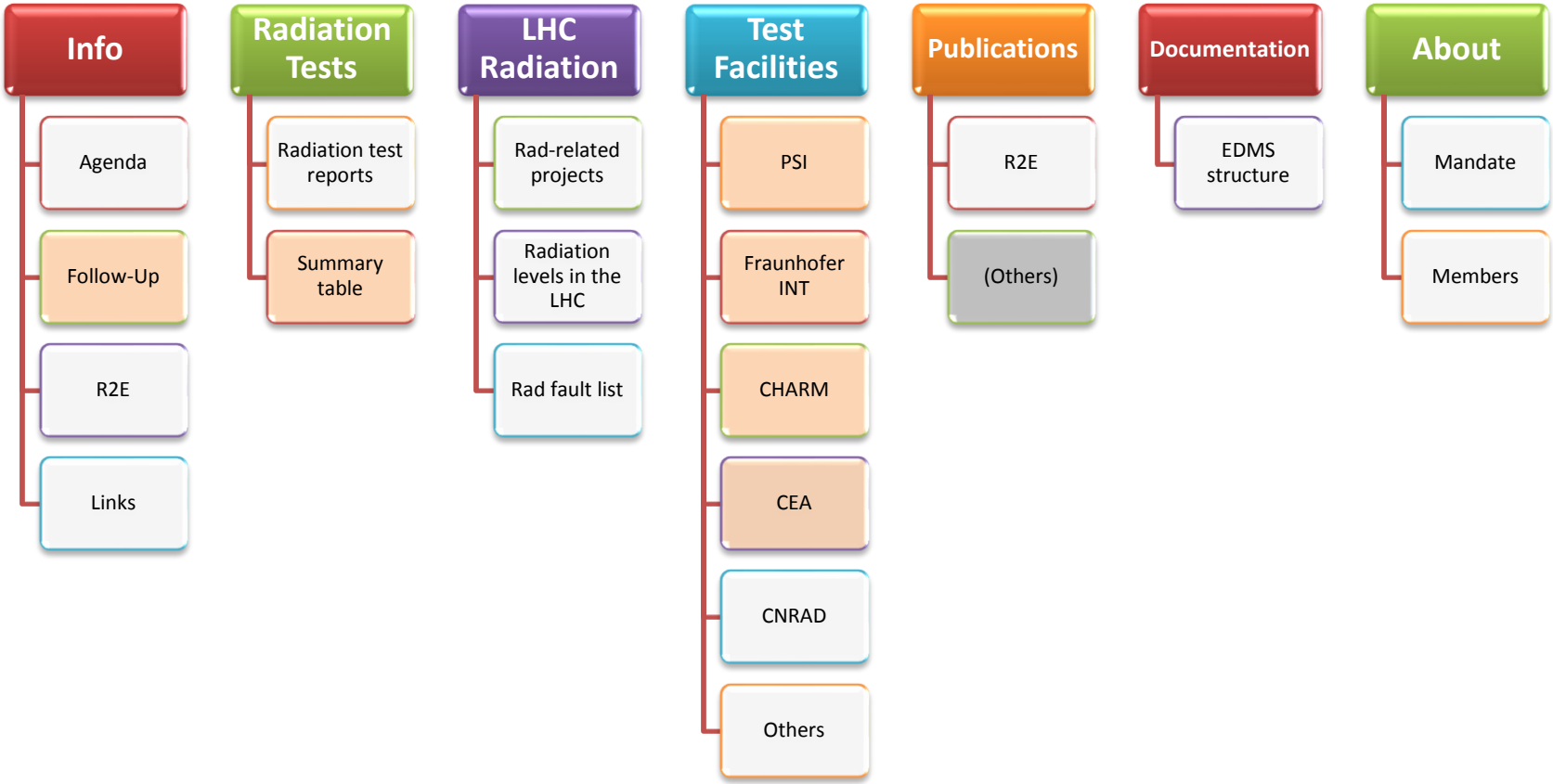
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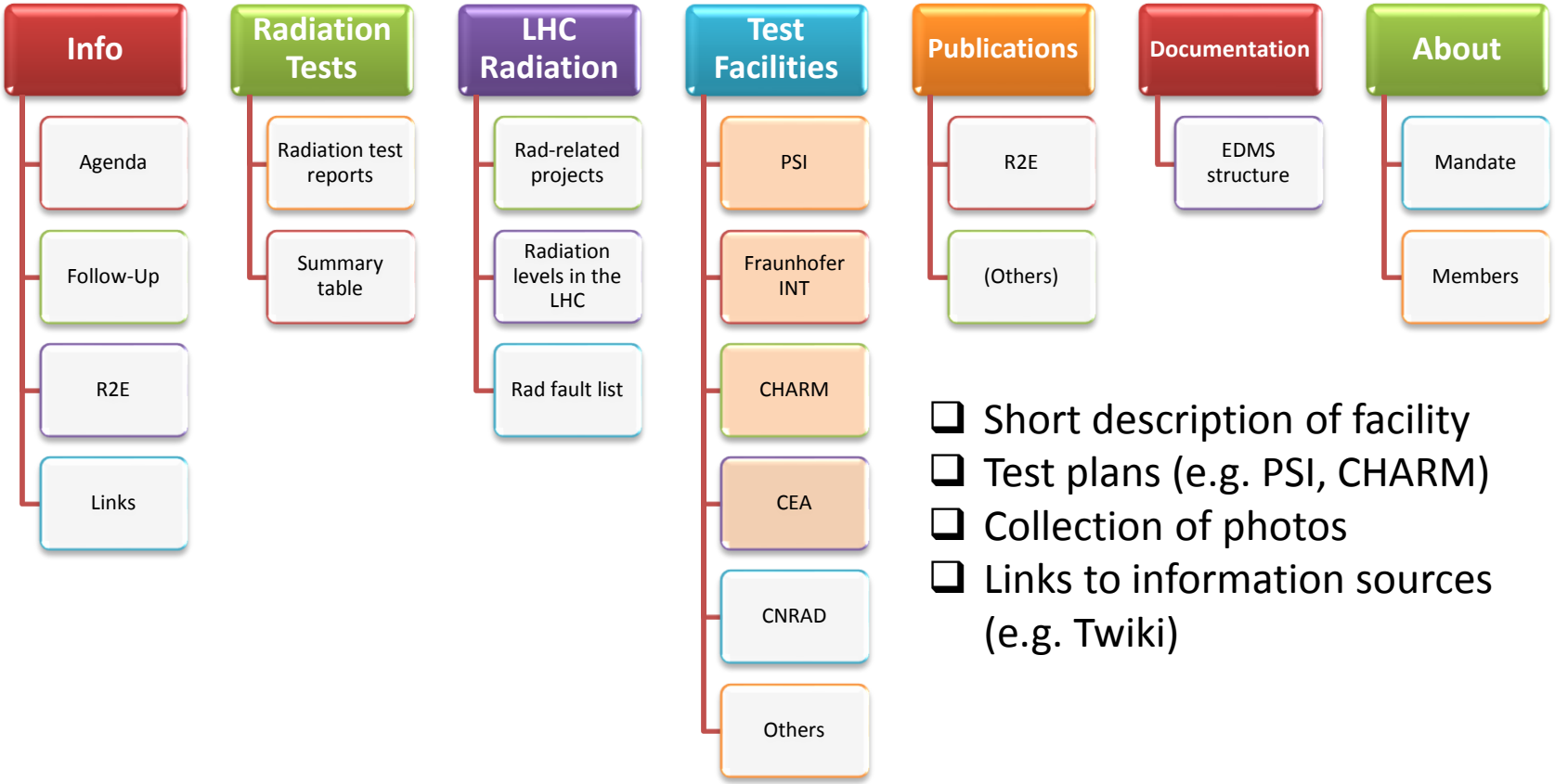
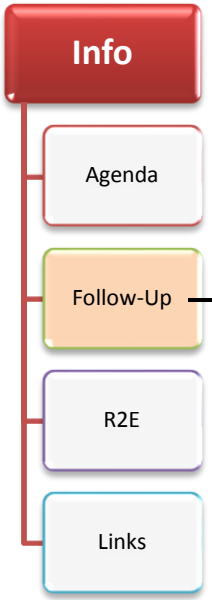


- ❑ Short description of facility
- ❑ Test plans (e.g. PSI, CHARM)
- ❑ Collection of photos
- ❑ Links to information sources (e.g. Twiki)

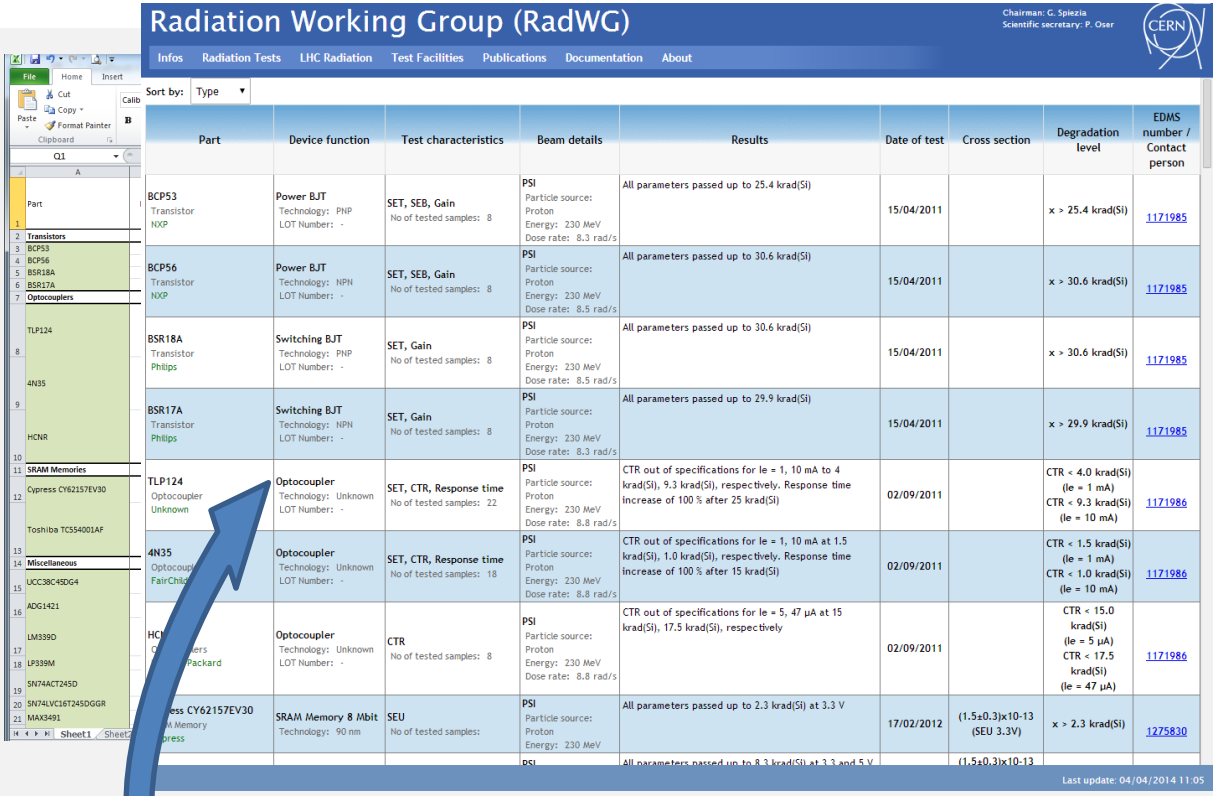
What is new?



- Track of questions/discussions/decisions which came up during the RadWG
- Keep the overview!
- Reminder

What is new?

- **Info**
  - Agenda
  - Follow-Up
  - R2E
  - Links
- **Radiation Tests**
  - Radiation test reports
  - Summary table



Radiation Working Group (RadWG)

Chairman: G. Spiezia
Scientific secretary: P. Oser

Infos | Radiation Tests | LHC Radiation | Test Facilities | Publications | Documentation | About

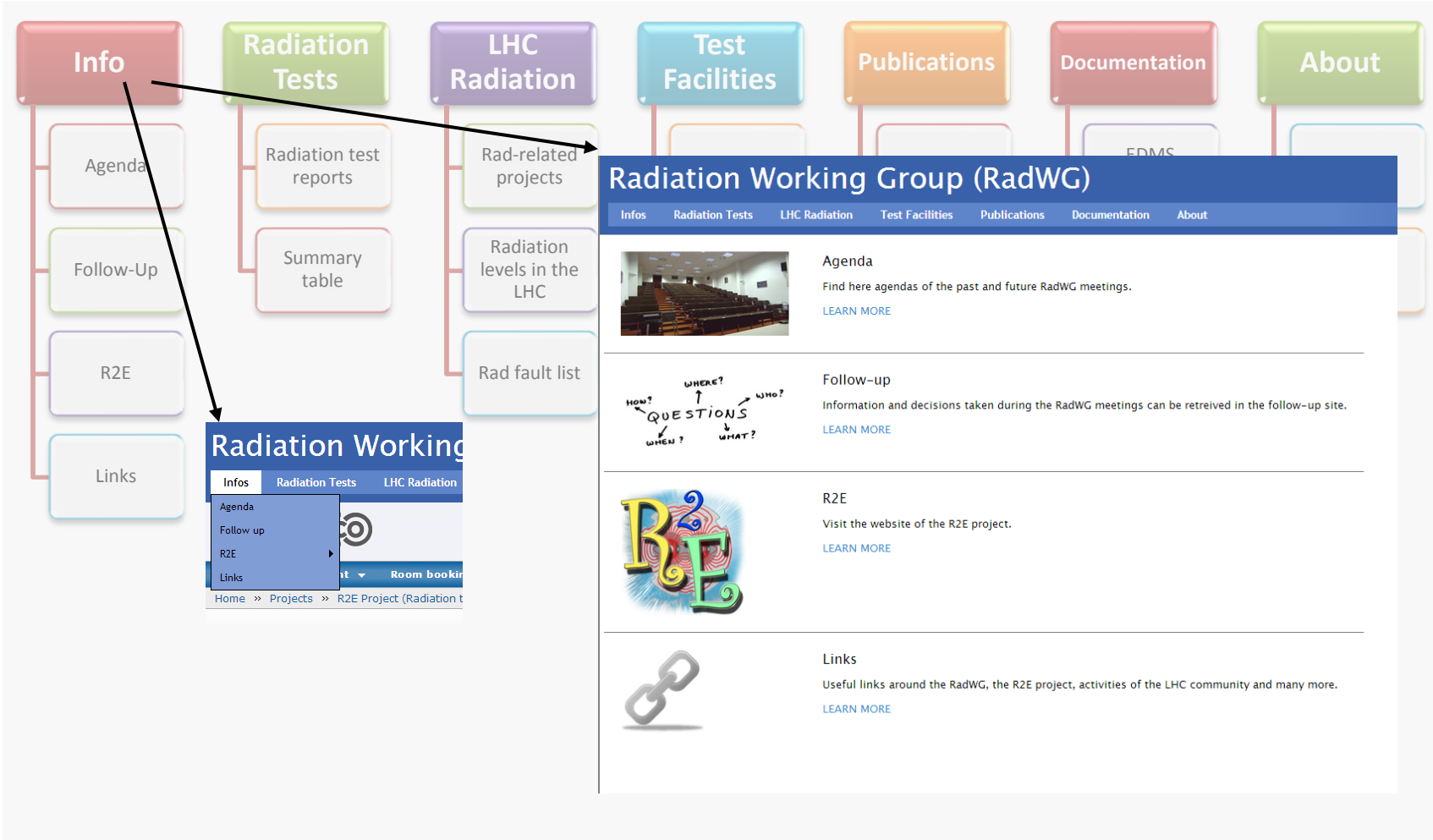
Sort by: Type

Part	Device function	Test characteristics	Beam details	Results	Date of test	Cross section	Degradation level	EDMS number / Contact person
BCP53 Transistor NXP	Power BJT Technology: PNP LOT Number: -	SET, SEB, Gain No of tested samples: 8	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.3 rad/s	All parameters passed up to 25.4 krad(Si)	15/04/2011		x > 25.4 krad(Si)	1171985
BCP56 Transistor NXP	Power BJT Technology: NPN LOT Number: -	SET, SEB, Gain No of tested samples: 8	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.5 rad/s	All parameters passed up to 30.6 krad(Si)	15/04/2011		x > 30.6 krad(Si)	1171985
BSR18A Transistor Philips	Switching BJT Technology: PNP LOT Number: -	SET, Gain No of tested samples: 8	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.5 rad/s	All parameters passed up to 30.6 krad(Si)	15/04/2011		x > 30.6 krad(Si)	1171985
BSR17A Transistor Philips	Switching BJT Technology: NPN LOT Number: -	SET, Gain No of tested samples: 8	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.3 rad/s	All parameters passed up to 29.9 krad(Si)	15/04/2011		x > 29.9 krad(Si)	1171985
TLP124 Optocoupler Unknown	Optocoupler Technology: Unknown LOT Number: -	SET, CTR, Response time No of tested samples: 22	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.8 rad/s	CTR out of specifications for Ie = 1, 10 mA to 4 krad(Si), 9.3 krad(Si), respectively. Response time increase of 100 % after 25 krad(Si)	02/09/2011		CTR < 4.0 krad(Si) (Ie = 1 mA) CTR < 9.3 krad(Si) (Ie = 10 mA)	1171986
4N35 Optocoupler FairChild	Optocoupler Technology: Unknown LOT Number: -	SET, CTR, Response time No of tested samples: 18	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.8 rad/s	CTR out of specifications for Ie = 1, 10 mA at 1.5 krad(Si), 1.0 krad(Si), respectively. Response time increase of 100 % after 15 krad(Si)	02/09/2011		CTR < 1.5 krad(Si) (Ie = 1 mA) CTR < 1.0 krad(Si) (Ie = 10 mA)	1171986
HCl ers Packard	Optocoupler Technology: Unknown LOT Number: -	CTR No of tested samples: 8	PSI Particle source: Proton Energy: 230 MeV Dose rate: 8.8 rad/s	CTR out of specifications for Ie = 5, 47 µA at 15 krad(Si), 17.5 krad(Si), respectively	02/09/2011		CTR < 15.0 krad(Si) (Ie = 5 µA) CTR < 17.5 krad(Si) (Ie = 47 µA)	1171986
ess CY62157EV30 M Memory press	SRAM Memory 8 Mbit Technology: 90 nm	SEU No of tested samples:	PSI Particle source: Proton Energy: 230 MeV	All parameters passed up to 2.3 krad(Si) at 3.3 V	17/02/2012	(1.5±0.3)x10-13 (SEU 3.3V)	x > 2.3 krad(Si)	1275830
				All parameters passed up to 8.3 krad(Si) at 3.3 and 5 V		(1.5±0.3)x10-13		

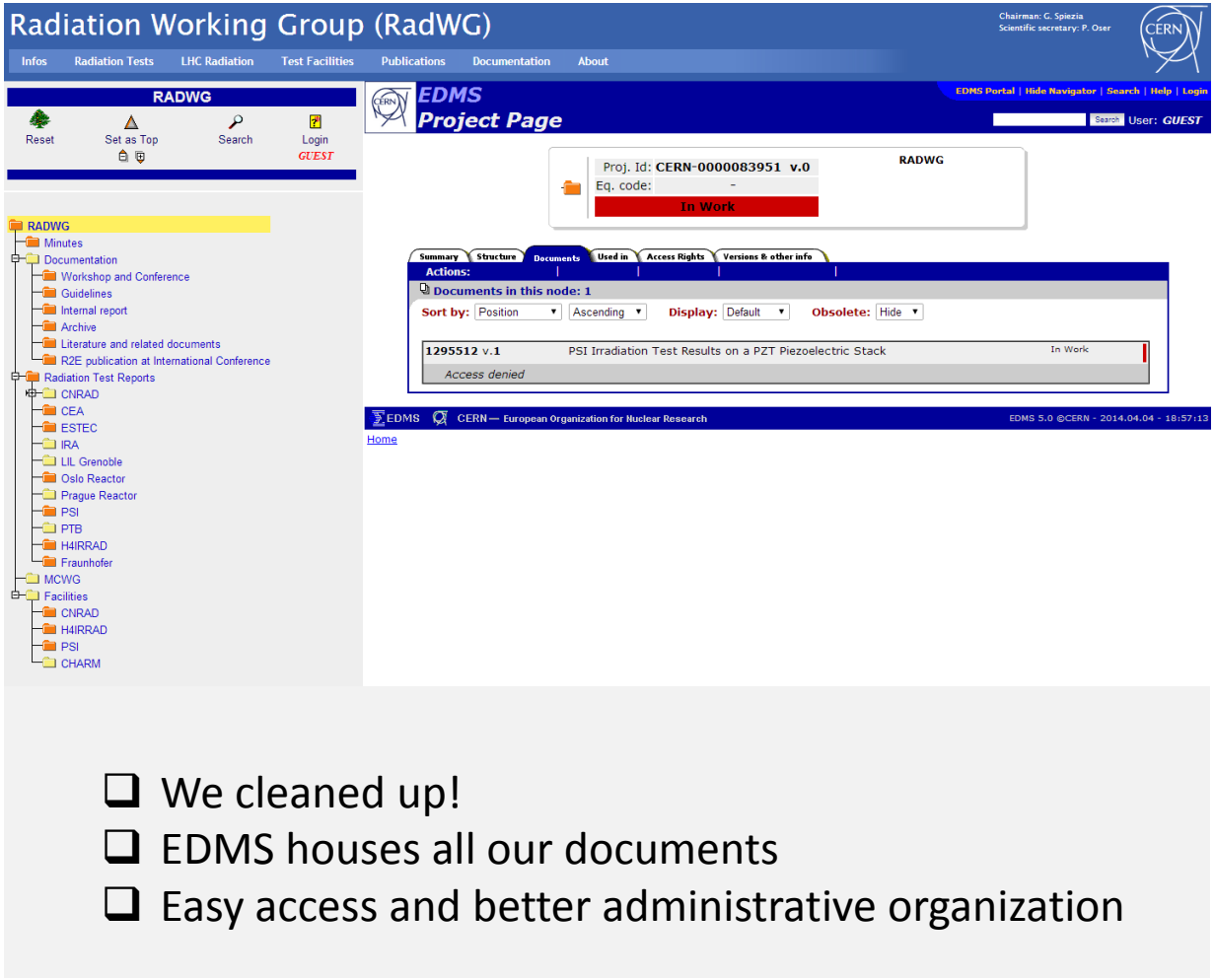
Last update: 04/04/2014 11:05

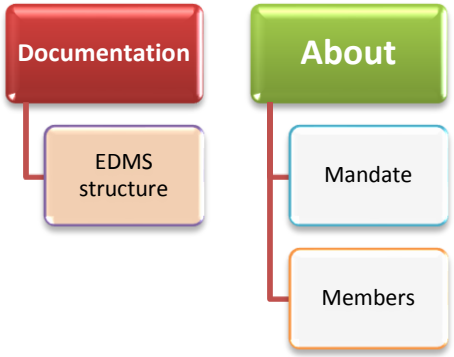
- Direct implementation into the website
- Sorting possible
- Easy access to database file
- Nothing to do, summary table is created & updated automatically

How is the website organized?



EDMS structure





- ❑ We cleaned up!
- ❑ EDMS houses all our documents
- ❑ Easy access and better administrative organization

Don’t hesitate to provide any feedback to me:

pascal.oser@cern.ch

Thank you for your attention!